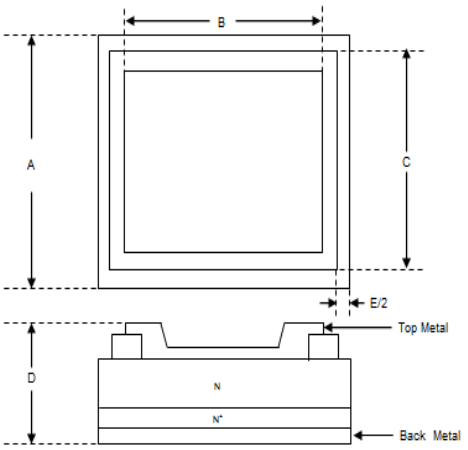
PMB032T045SS-255A

1A/45V(1), low VF Planar MOS Barrier Diode

Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	814μm	32.0 mil
	Top Metal Pad Size (B)	712 μm	28.0mil
	Chip Size (C)	/	/
	Wafer Thickness (D)	255 μm	10.0 mil
	Scribe Line Width (E)	80 μm	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	PMB032T045SS-255A	Ag
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23℃±3℃)	

Electrical Characteristics (T_J=25℃, unless otherwise specified) (2)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V_{BR}	Reverse Breakdown Voltage	46	52	-	V	I_R =300μA
V_F	Instantaneous Forward Voltage	-	0.41	0.46	V	I_F =1A(3)
I_R	Reverse Leakage Current	-	100	200	μA	V_R =45V
T_J, T_{STG}	Operating and Storage Temperature	-40℃ to 150℃ Max				

Note:

(1) The preliminary wafer datasheet only for reference;

(2) This characteristics assumes the dies are assembled in SMA packages. Actual performance may degrade when assembled. YJ does not guarantee device performance after assembly;

(3) Pulse Width tp = < 300μS, Duty Cycle <2%;